

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20160408001 Qualification of Additional Fab (RFAB) and Additional Assembly/Test (TI Clark) sites for Select Devices Change Notification / Sample Request

Date: 4/12/2016

To: Newark/Farnell PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN_ww_admin_team@list.ti.com).

Sincerely,

PCN Team SC Business Services

20160408001 Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE

CUSTOMER PART NUMBER

null null

TLV320AIC3106IRGZT TLV320AIC3106IRGZR

Technical details of this Product Change follow on the next page(s).

	PCN Number:		20	20160408001 PCN Date: 4/12/20						.6					
Title: Qualification Select Device				Add	itional	Fab (RF	AB) ar	nd Add	litional	Ass	embly	/Test (TI Cla	rk) sites fo	r
Customer Contact:		PC	PCN Manager Dept: Quality Services				S								
Proposed 1 st Ship Da			ate:	te: 7/12/2016 Estimated Sample Availability: Provided Request					rided upon uest						
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H	☑ Design☒ Test Site			\forall		Electrical Specification Packing/Shipping/Labeling			Mechanical Specification Test Process						
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Wafer Fab Site									Wafer Fab Process						
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	Wha	ıt (Packag	e De	esig	nator))	MLA		С	RS			TI CI	ark	
		nt Compou				42	205846	5	SID#			_	4207		
	Mour	nt Compou	nd (R	(GZ)		n/a		SID#	435	143		<u> 4207</u>	123	
	Fab [Details													
	Current Fab		Pr	oce	ss	Wafe Diame			tional		Proce	ess	Wafer		
Site					Diame								meter		
	ח	D1DM5		<u>C05</u>		200 m			Site		COS		Dia 30		
	DI	P1DM5		C05		200 m			Site AB		C05			0 mm	
test Rea	cover MQ.	rage, insert	ions,				nm	RF	AB	n cu			30	0 mm	
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Fab Sites				
Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	
DP1DM5	DM5	USA	Dallas	
New				
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	
RFAB	RFB	USA	Richardson	

Sample product shipping label (not actual product label)



Topside Device marking:

Assembly site code for MLA= K Assembly site code for CRS = W Assembly site code for QAB = I

Product Affected							
	Т	1	Т				
TLV320AIC3004IRHBR	TLV320AIC3105IRHBR	TLV320AIC3106IRGZR	TLVAIC3105IRHBRG4				
TLV320AIC3004IRHBT	TLV320AIC3105IRHBT	TLV320AIC3106IRGZT					



TI Information Selective Disclosure

Qualification Report

TLV320AIC3106/5/6RGZ in RFAB and Clark (release the G2TIAIC39A die in Clark) Approve Date 05-Apr-2016 Product Attributes

Attributes	Qual Device: TLV320AIC3106IRGZR	QBS Process Reference: VSP6825BZRC	QBS Package Reference: SN65LVCP40RGZ	QBS Package Reference: TPS62402DRCR _CU_WIRE
Assembly Site	CLARK-AT	PHI	CLARK-AT	CLARK-AT
Package Family	QFN	JRBGA	QFN	SON
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	RFAB	HIJI, RFAB	FFAB	FFAB
Wafer Process	1118C05	1833C05, LBC4	BICOM3	3370A12

⁻ QBS: Qual By Similarity

⁻ Qual Device TLV320AIC3106IRGZR is qualified at LEVEL2-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TLV320AIC3106IRGZR	QBS Process Reference: VSP6825BZRC	QBS Package Reference: SN65LVCP40RGZ	QBS Package Reference: TPS62402DRCR _CU_WIRE
AC	Autoclave 121C	96 Hours	-	-	1/77/0	1/77/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass	-	-	-
HAST	Biased HAST,130C/85%RH	96 Hours	-	3/230/0	1/77/0	-
HTOL	Life Test, 140C	480 Hours	-	3/231/0	-	-
HTOL	Life Test, 155C	240 Hours	-	=	1/77/0	-
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	3/231/0	1/77/0	1/77/0
PD	Physical Dimensions		-	=	1/5/0	1/5/0
TC	Temperature Cycle, - 65/150C	500 Cycles	-	3/231/0	1/77/0	1/77/0
TS	Thermal Shock, - 65/150C	500 Cycles	-	-	-	1/77/0
WBP	Bond Pull	Wires	1/76/0	-	1/76/0	1/76/0
WBS	Wire Bond Shear	Wires	1/76/0	=	1/76/0	1/76/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
 The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
 The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com